

FS10KM-12A

HIGH-SPEED SWITCHING USE

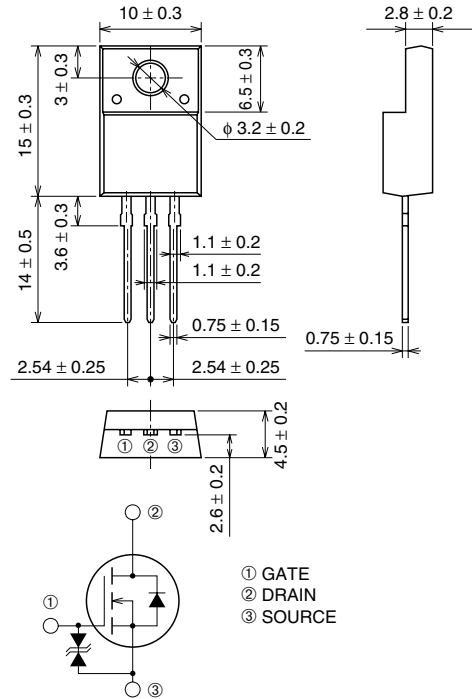
FS10KM-12A



- 10V DRIVE
- V_{DS} 600V
- $r_{DS(ON)}$ (MAX) 0.94Ω
- I_D 10A

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

SMPS, AC-adaptor, Power supply of Printer, Copier, TV, VCR. etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	600	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	±30	V
I_D	Drain current		10	A
I_{DM}	Drain current (Pulsed)		30	A
I_{DA}	Avalanche current (Pulsed)	$L = 200\mu H$	10	A
P_D	Maximum power dissipation		35	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
V_{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

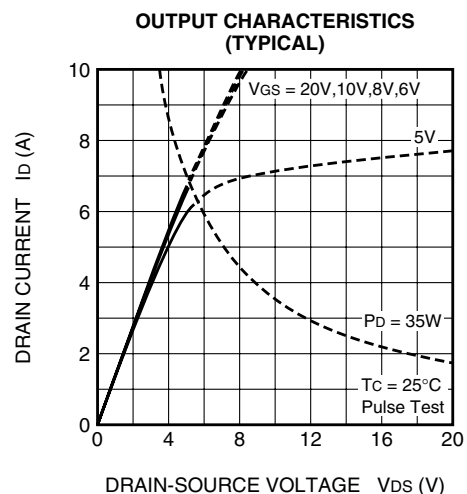
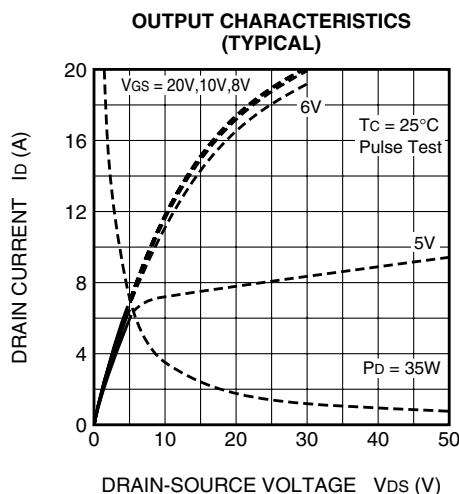
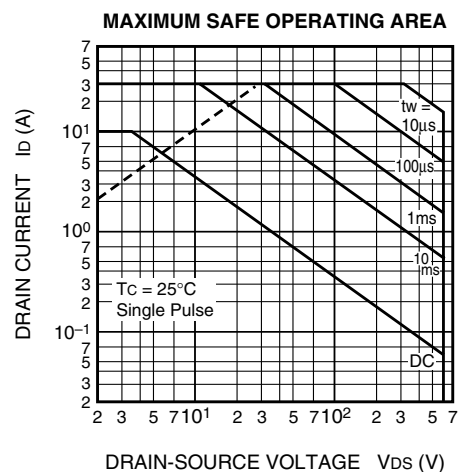
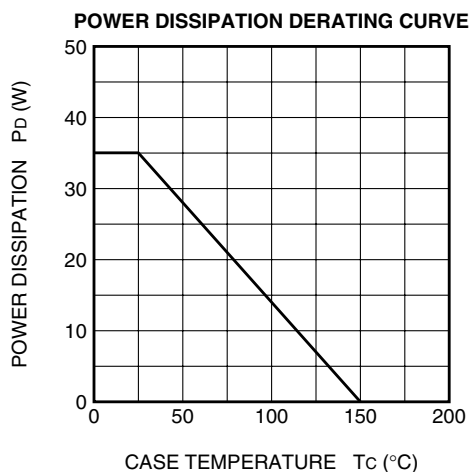
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ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	600	—	—	V
V (BR) GSS	Gate-source breakdown voltage	I _{GS} = ±100μA, V _{DS} = 0V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25V, V _{DS} = 0V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 600V, V _{GS} = 0V	—	—	1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	2.5	3.0	3.5	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 5A, V _{GS} = 10V	—	0.72	0.94	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 5A, V _{GS} = 10V	—	3.60	4.70	V
y _{fs}	Forward transfer admittance	I _D = 5A, V _{DS} = 10V	6.0	10.0	—	S
C _{iss}	Input capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	—	1500	—	pF
C _{oss}	Output capacitance		—	130	—	pF
C _{rss}	Reverse transfer capacitance		—	35	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 200V, I _D = 5A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	25	—	ns
t _r	Rise time		—	35	—	ns
t _d (off)	Turn-off delay time		—	190	—	ns
t _f	Fall time		—	50	—	ns
V _{SD}	Source-drain voltage	I _S = 5A, V _{GS} = 0V	—	1.5	2.0	V
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	3.57	°C/W

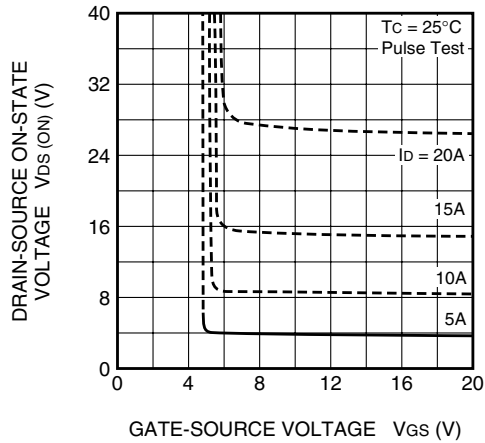
PERFORMANCE CURVES



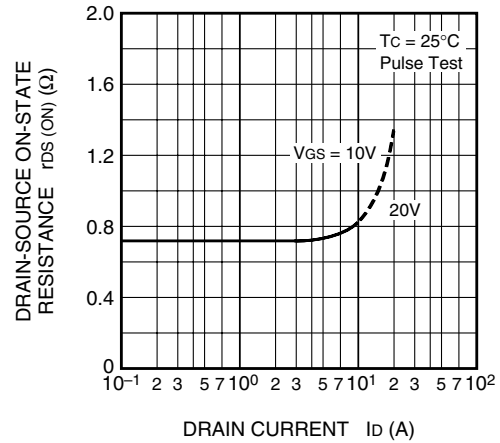
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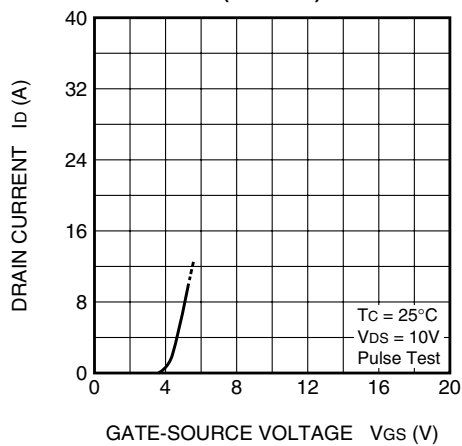
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



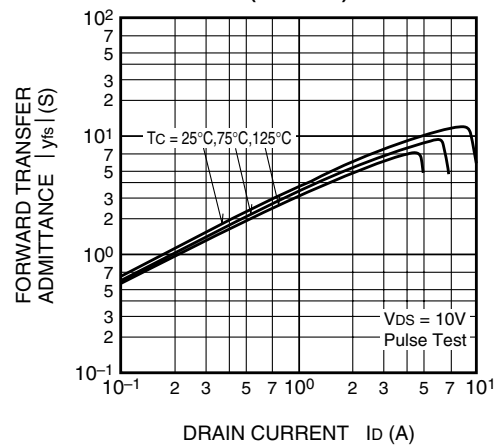
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



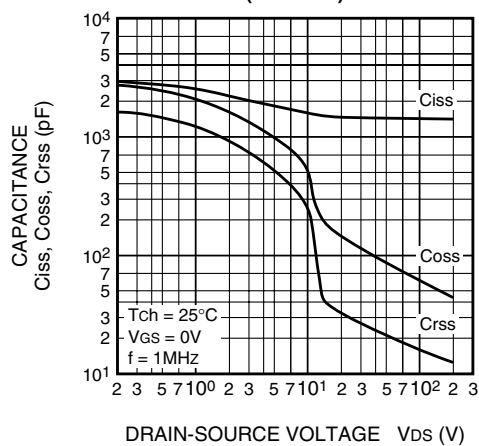
TRANSFER CHARACTERISTICS
(TYPICAL)



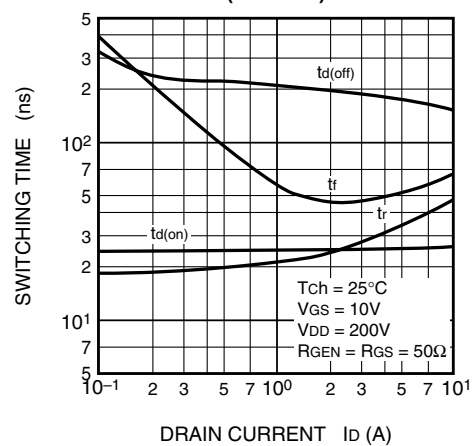
FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)



CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)



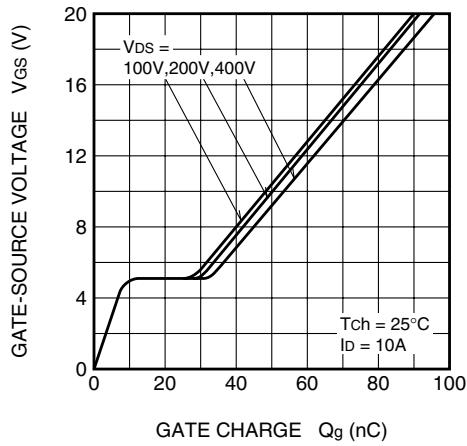
SWITCHING CHARACTERISTICS
(TYPICAL)



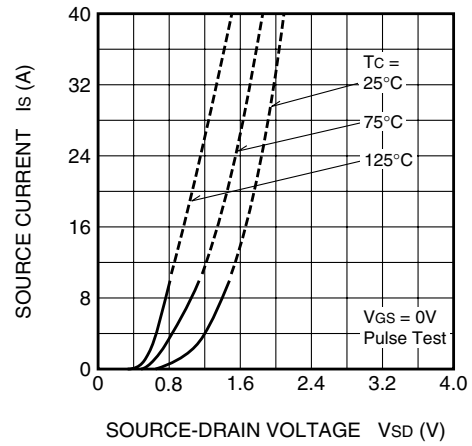
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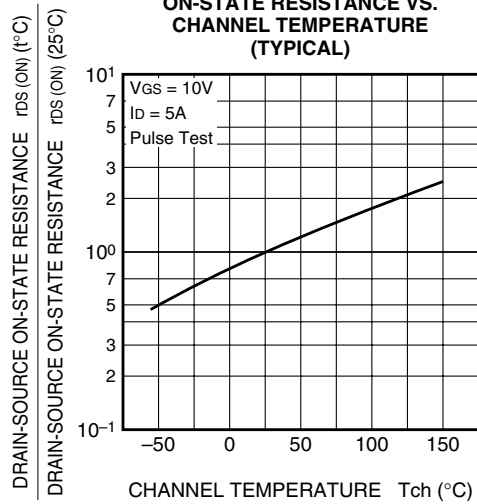
**GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)**



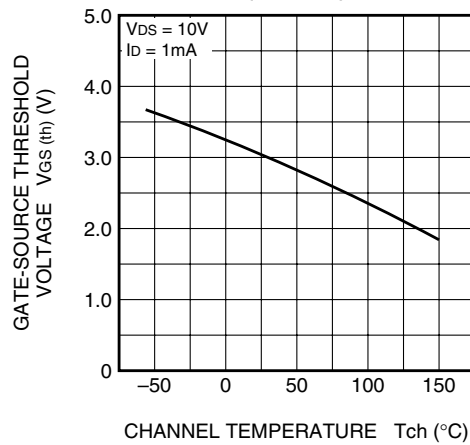
**SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



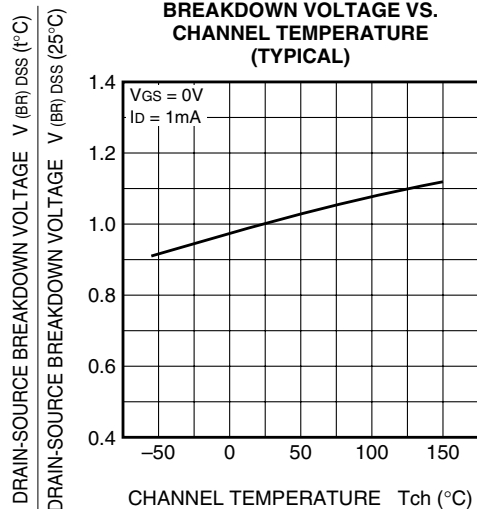
**ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**

